

## P-Channel 12-V (D-S) MOSFET

MOSFET PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
- 12	0.035 at V <sub>GS</sub> = - 4.5 V	- 5.1	9 nC
	0.045 at V <sub>GS</sub> = - 2.5 V	- 4.5	
	0.059 at V <sub>GS</sub> = - 1.8 V	- 3.9	

### FEATURES

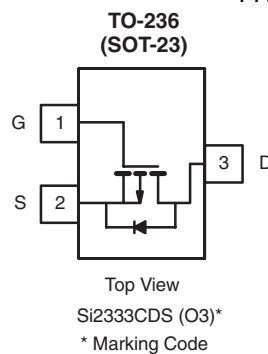
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Load Switch
- PA Switch



Ordering Information: Si2333CDS-T1-E3 (Lead (Pb)-free)  
Si2333CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	- 12	V
Gate-Source Voltage	V <sub>GS</sub>	± 8	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 7.1
		T <sub>C</sub> = 70 °C	- 5.7
		T <sub>A</sub> = 25 °C	- 5.1 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	- 4.0 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	- 20	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	- 0.63 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	2.5
		T <sub>C</sub> = 70 °C	1.6
		T <sub>A</sub> = 25 °C	1.25 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.8 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	≤ 5 s	R <sub>thJA</sub>	75	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	40	50	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under Steady State conditions is 166 °C/W.

MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-12			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-13		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -5.1\text{ A}$		0.0285	0.035	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -4.5\text{ A}$		0.036	0.045	
		$V_{GS} = -1.8\text{ V}, I_D = -2.0\text{ A}$		0.046	0.059	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -5\text{ V}, I_D = -5.3\text{ A}$		18.5		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1225		pF
Output Capacitance	$C_{oss}$			315		
Reverse Transfer Capacitance	$C_{rss}$			260		
Total Gate Charge	$Q_g$	$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5.1\text{ A}$		15	25	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -6\text{ V}, V_{GS} = -2.5\text{ V}, I_D = -5.1\text{ A}$		9	15	
Gate-Drain Charge	$Q_{gd}$			1.9		
Gate Resistance	$R_g$		$f = 1\text{ MHz}$		4.0	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 6\text{ }\Omega$ $I_D = -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 1\text{ }\Omega$		13	20	ns
Rise Time	$t_r$			35	60	
Turn-Off Delay Time	$t_{d(off)}$			45	70	
Fall Time	$t_f$			12	20	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-1.0	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-20	
Body Diode Voltage	$V_{SD}$	$I_S = -1.0\text{ A}$		-0.7	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		32	50	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			20	40	nC
Reverse Recovery Fall Time	$t_a$			16		ns
Reverse Recovery Rise Time	$t_b$			16		

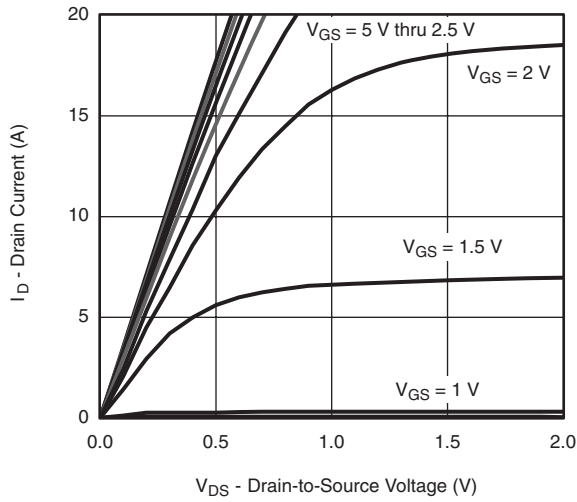
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

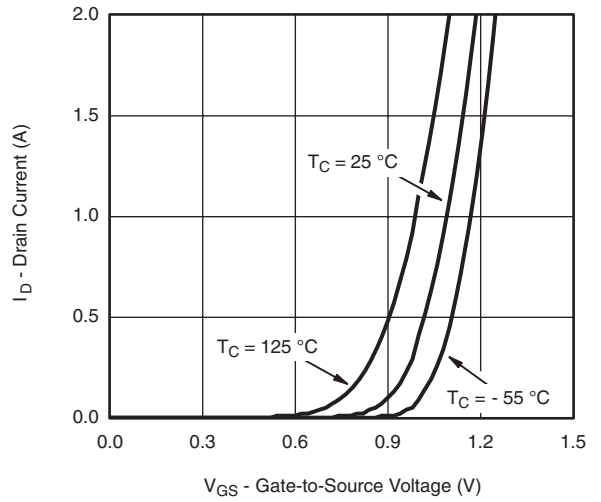
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

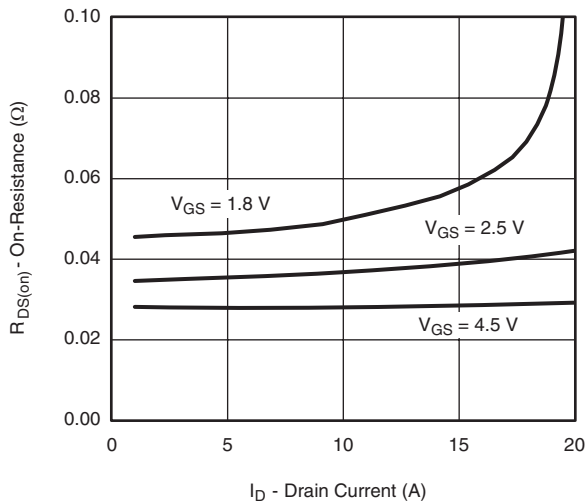
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



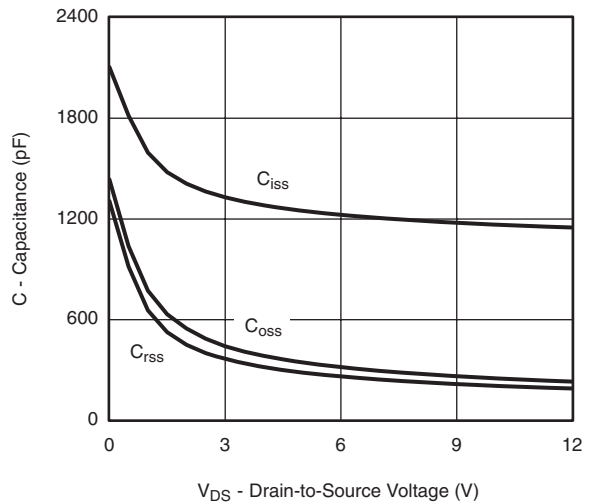
**Output Characteristics**



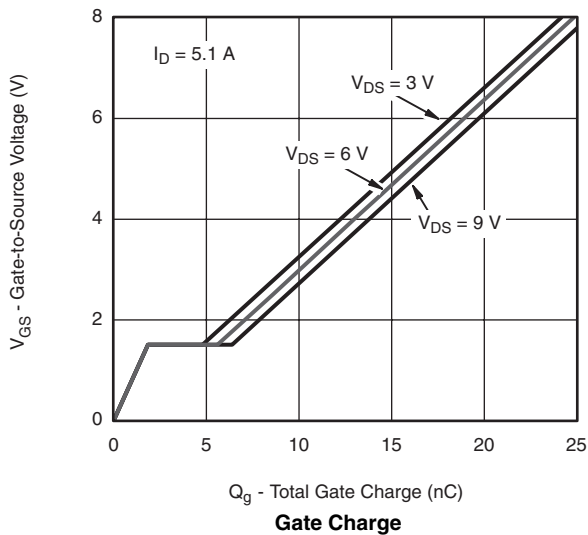
**Transfer Characteristics**



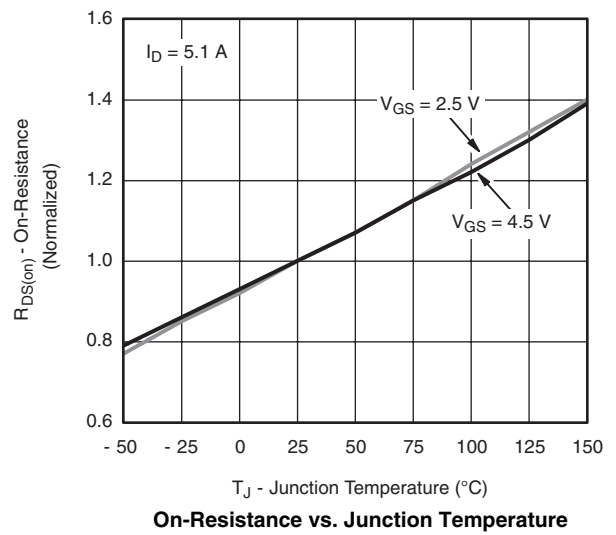
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

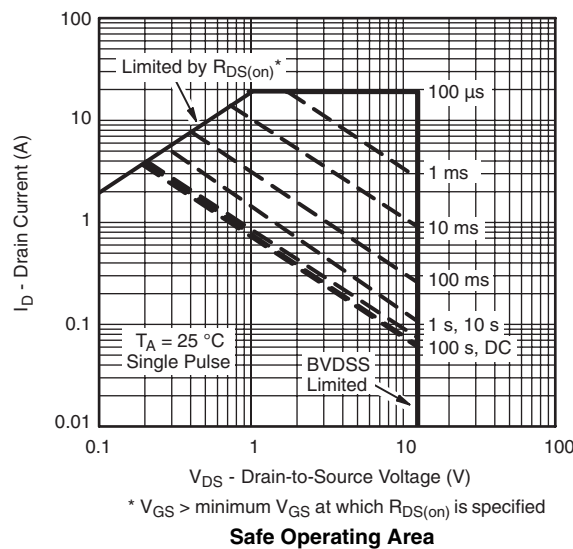
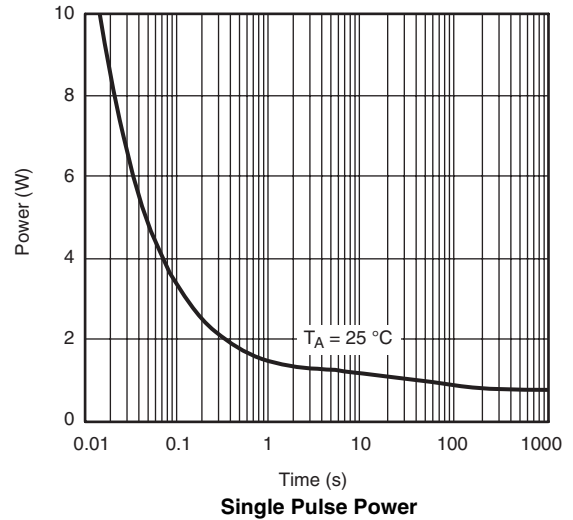
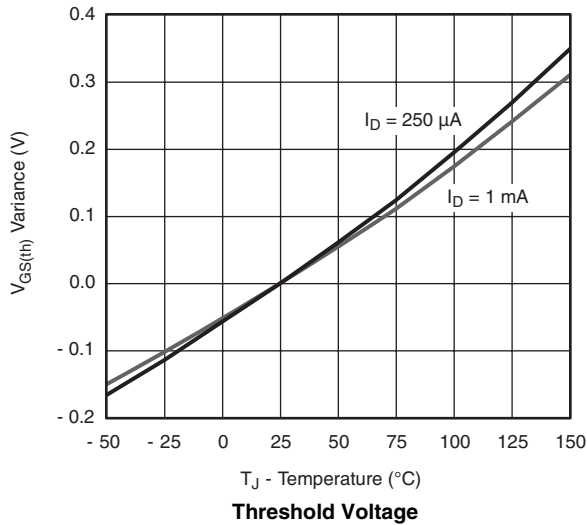
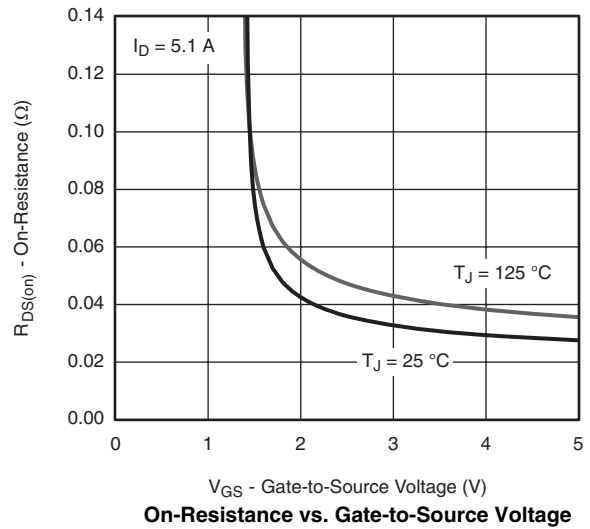
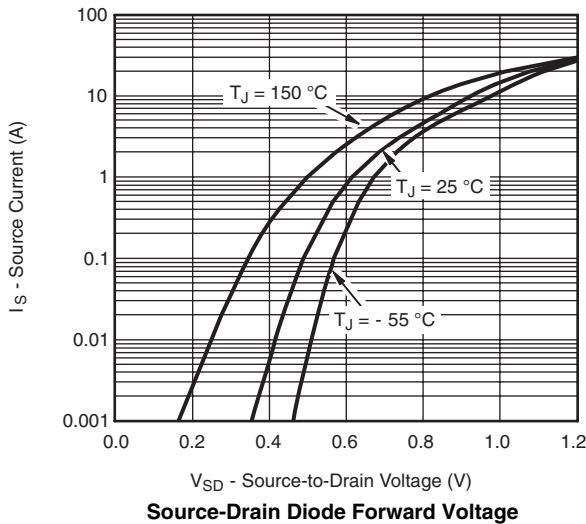


**Gate Charge**

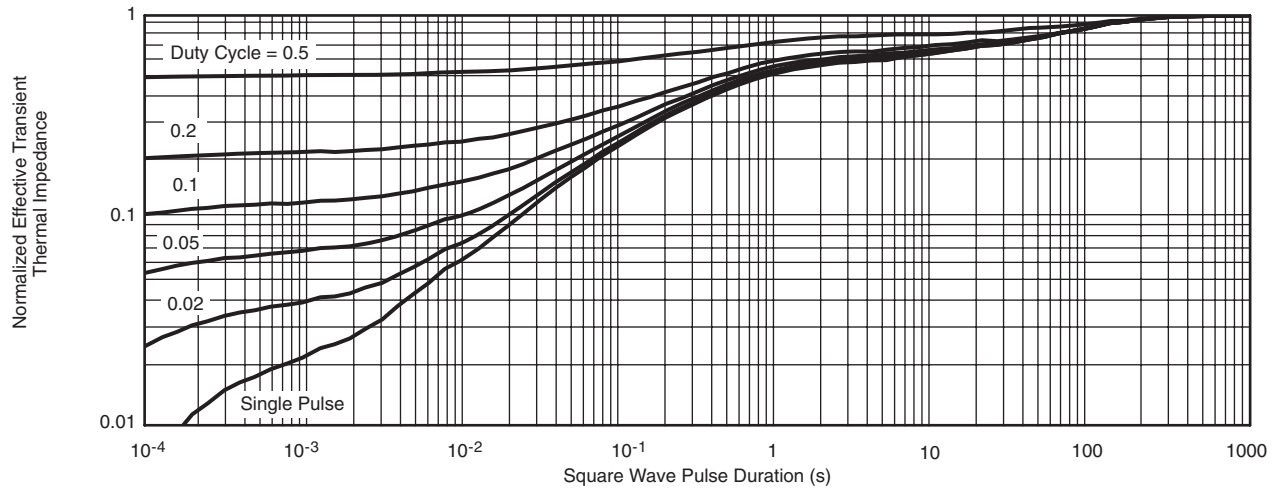


**On-Resistance vs. Junction Temperature**

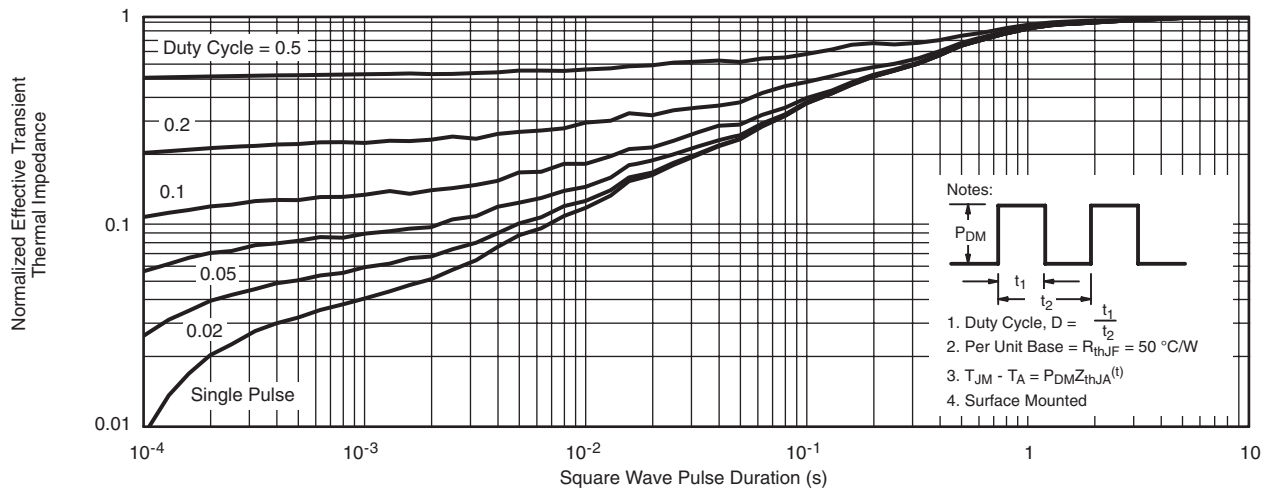
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

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